

ABSTRACT OF THE DISCLOSURE

**METHOD FOR FABRICATING A CRYSTALLINE ALKALINE EARTH
METAL OXIDE INTERFACE WITH SILICON**

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A method for fabricating a semiconductor structure comprises the steps of providing a silicon substrate (10) having a surface (12); forming on the surface of the silicon substrate an interface (14) comprising a single atomic layer of silicon, oxygen, and a metal; and forming one or more layers of a single crystal oxide (26) on the interface. The interface comprises an atomic layer of silicon, oxygen, and a metal in the form XSiO_2 , where X is a metal.

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Fig. 10 to accompany abstract.

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